

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2N5632 2N5633 2N5634

DESCRIPTION

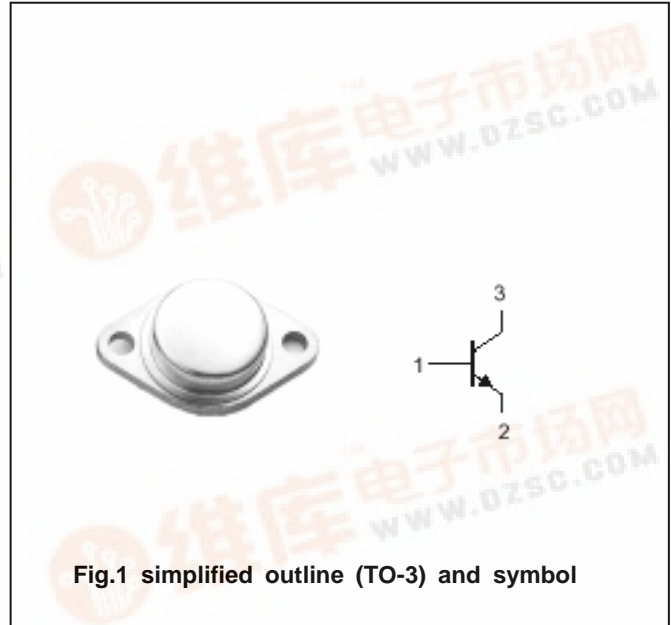
- With TO-3 package
- Low collector saturation voltage
- High DC current gain

APPLICATIONS

- For general-purpose power amplifier and switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2N5632	100	V
		2N5633	120	
		2N5634	140	
V _{CEO}	Collector-emitter voltage	2N5632	100	V
		2N5633	120	
		2N5634	140	
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		10	A
P _D	Total Power Dissipation	T _C =25	150	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-65~200	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance junction to case	1.1	/W

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT	
V _{CE0(SUS)}	Collector-emitter sustaining voltage	2N5632	100			V	
		2N5633	120				
		2N5634	140				
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =7A; I _B =0.7A			1.0	V	
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =10A; I _B =2A			3.0	V	
V _{BEsat}	Base-emitter saturation voltage	I _C =10A; I _B =2A			2.5	V	
V _{BE}	Base-emitter on voltage	I _C =5A; V _{CE} =5V			1.5	V	
I _{CEO}	Collector cut-off current	2N5632	V _{CE} =50V; I _B =0			1.0	mA
		2N5633	V _{CE} =60V; I _B =0				
		2N5634	V _{CE} =70V; I _B =0				
I _{CEV}	Collector cut-off current	V _{CE} =ratedV _{CB} ; V _{BE(off)} =1.5V T _C =150			1.0 5.0	mA	
I _{EBO}	Emitter cut-off current	V _{EB} =7V; I _C =0			1.0	mA	
h _{FE}	DC current gain	2N5632	I _C =5A; V _{CE} =5V	25		100	
		2N5633		20		80	
		2N5634		15		60	
f _T	Transition frequency	I _C =1A; V _{CE} =20V	1.0			MHz	

PACKAGE OUTLINE

